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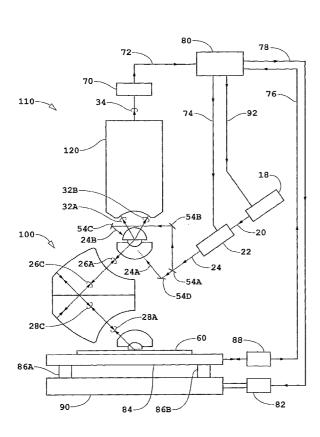
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(54) Title: SUB-NANOMETER OVERLAY, CRITICAL DIMENSION, AND LITHOGRAPHY TOOL PROJECTION OPTIC METROLOGY SYSTEMS BASED ON MEASUREMENT OF EXPOSURE INDUCED CHANGES IN PHOTORESIST ON WAFERS



(57) Abstract: A method of processing a substrate on which a layer of photoresist has been applied, the method involving: exposing the layer of photoresist to patterned radiation to generate exposure-induced changes in the layer of photoresist which form patterns having one or more features; and before developing the exposed photoresist, interferometrically obtaining measurements of the pattern in the exposed layer of photoresist for determining locations of the one or more features of the pattern.



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FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched			
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C. DOCUMENTS CONSIDERED TO BE RELEVANT		T 1 1 N	
Category * Citation of document, with indication, where a		Relevant to claim No.	
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Further documents are listed in the continuation of Box C.	See patent family annex.	enational filing date or priority	
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Continuation of B. FIELDS SEARCHED Item 3:	
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search terms: interference, wafer, substrate, resist, photoresist, exposure, developi	ing
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